CLAIMS:

1. A method of depositing an antimony-comprising phase change material onto a substrate, comprising providing a reducing agent and vaporized $Sb(OR)_3$ to a substrate, where R is alkyl, and forming there-from antimony-comprising phase change material on the substrate, the phase change material having no greater than 10 atomic percent oxygen and comprising another metal in addition to antimony.

2. The method of claim 1 wherein the substrate temperature while the reducing agent and the vaporized $Sb(OR)_3$ are provided to the substrate is no greater than 450°C.

3. The method of claim 1 wherein the forming produces the phase change material to have no greater than 5 atomic percent oxygen.

4. The method of claim 1 wherein the forming produces the phase change material to have no greater than 1 atomic percent oxygen.

5. The method of claim 1 wherein the forming produces the phase change material to have no detectable oxygen therein.

6. The method of claim 1 wherein the reducing agent and the $Sb(OR)_3$ are provided to the substrate at the same time.

7. The method of claim 1 wherein the reducing agent comprises at least one of NH_3, H_2, CH_2O, and CH_2O_2.

8. The method of claim 1 wherein the reducing agent and the $Sb(OR)_3$ are provided to the substrate at different times.

9. The method of claim 1 wherein the another metal comprises Ge.

10. The method of claim 1 wherein the another metal comprises Te.

11. The method of claim 1 wherein the another metal comprises Ge and Te.

12. The method of claim 1 wherein the another metal comprises at least one of In, Se, Ga, B, Sn, and Ag.

13. The method of claim 1 wherein the forming comprises chemical vapor deposition.

14. The method of claim 13 wherein the chemical vapor deposition is in the absence of plasma.

15. The method of claim 13 wherein the chemical vapor deposition is plasma enhanced.

16. The method of claim 13 wherein the another metal comprises Ge, and comprising providing a Ge-comprising precursor to the substrate at the same time as providing the $Sb(OR)_3$ to the substrate.

17. The method of claim 13 wherein the another metal comprises Te, and comprising providing a Te-comprising precursor to the substrate at the same time as providing the $Sb(OR)_3$ to the substrate.

18. The method of claim 13 wherein the another metal comprises Ge and Te, and comprising providing both a Ge-comprising precursor to the substrate and a Te-comprising precursor to the substrate at the same time as providing the $Sb(OR)_3$ to the substrate.

19. The method of claim 1 wherein the forming comprises atomic layer deposition.

20. The method of claim 1 wherein the forming of the antimony-comprising phase change material comprises:

forming a monolayer comprising $Sb(OR)_x$ onto the substrate from the $Sb(OR)_3$, where "x" is less than 3; and

after forming the monolayer, providing the reducing agent to the monolayer to remove OR ligand from the Sb.

21. A method of forming phase change memory circuitry, comprising:

forming inner electrode material over a substrate;

depositing an antimony-comprising phase change material over the inner electrode material, the depositing comprising providing a reducing agent and vaporized $Sb(OR)_3$ over the inner electrode material, where R is alkyl, and forming there-from antimony-comprising phase change material over the inner electrode material, the phase change material having no greater than 10 atomic percent oxygen and comprising another metal in addition to antimony; and

forming outer electrode material over the antimony-comprising phase change material.

22. The method of claim 21 comprising forming the antimony-comprising phase change material in direct physical touching contact with the inner electrode material, and forming the outer electrode material in direct physical touching contact with the antimony-comprising phase change material.

23. The method of claim 21 wherein forming the antimony-comprising phase change material produces the phase change material to have no greater than 1 atomic percent oxygen.

24. The method of claim 21 wherein forming the antimony-comprising phase change material produces the phase change material to have no detectable oxygen therein.

25. The method of claim 21 wherein the forming of the antimony-comprising phase change material comprises:

forming a monolayer comprising $Sb(OR)_x$ onto the substrate from the $Sb(OR)_3$, where "x" is less than 3; and

after forming the monolayer, providing the reducing agent to the monolayer to remove OR ligand from the Sb.

CLAIMS

1. A method of depositing an antimony-comprising phase change material onto a substrate, comprising providing a reducing agent and vaporized compound consisting of $Sb(OR)_3$ to the substrate, where R is an alkyl, and forming there-from the antimony-comprising phase change material on the substrate, the antimony-comprising phase change material having no greater than 10 atomic percent of oxygen and comprising another metal in addition to antimony.

2. The method of claim 1 wherein the substrate temperature while the reducing agent and the vaporized $Sb(OR)_3$ are provided to the substrate is no greater than 450°C.

3. The method of claim 1 wherein the forming produces the antimony-comprising phase change material to have no greater than 5 atomic percent of the oxygen.

4. The method of claim 1 wherein the forming produces the antimony-comprising phase change material to have no greater than 1 atomic percent of the oxygen.

5. The method of claim 1 wherein the forming produces the antimony-comprising phase change material to have no detectable oxygen therein.

6. The method of claim 1 wherein the reducing agent and the $Sb(OR)_3$ are provided to the substrate at the same time.

7. The method of claim 1 wherein the reducing agent comprises at least one of NH_3, H_2, CH_2O, and CH_2O_2.

8. The method of claim 1 wherein the reducing agent and the $Sb(OR)_3$ are provided to the substrate at different times.

9. The method of claim 1 wherein the another metal comprises Ge.

10. The method of claim 1 wherein the another metal comprises Te.

11. The method of claim 1 wherein the another metal comprises Ge and Te.

12. The method of claim 1 wherein the another metal comprises at least one of In, Se, Ga, B, Sn, and Ag.

13. The method of claim 1 wherein the forming comprises chemical vapor deposition.

14. The method of claim 13 wherein the chemical vapor deposition is in an absence of plasma.

15. The method of claim 13 wherein the chemical vapor deposition is plasma enhanced.

16. The method of claim 13 wherein the another metal comprises Ge, and the method further comprises providing a Ge-comprising precursor to the substrate at a same time as providing the $Sb(OR)_3$ to the substrate.

17. The method of claim 13 wherein the another metal comprises Te, and the method further comprises providing a Te-comprising precursor to the substrate at a same time as providing the $Sb(OR)_3$ to the substrate.

18. The method of claim 13 wherein the another metal comprises Ge and Te, and the method further comprises providing both a Ge-comprising precursor to the substrate and a Te-comprising precursor to the substrate at a same time as providing the $Sb(OR)_3$ to the substrate.

19. The method of claim 1 wherein the forming comprises atomic layer deposition.

20. The method of claim 1 wherein the forming of the antimony-comprising phase change material comprises:

forming a monolayer onto the substrate from the $Sb(OR)_3$; and

after forming the monolayer, providing the reducing agent to the monolayer to remove ligands consisting of OR from the Sb to produce an Sb monolayer on the substrate.

21. A method of forming phase change memory circuitry, comprising:

forming an inner electrode material over a substrate;

depositing an antimony-comprising phase change material over the inner electrode material, the depositing comprising providing a reducing agent and vaporized compound consisting of $Sb(OR)_3$ over the inner electrode material, where R is an alkyl, and forming there-from the antimony-comprising phase change material over the inner electrode material, the antimony-comprising phase change material having no greater than 10 atomic percent of oxygen and comprising another metal in addition to antimony; and

forming an outer electrode material over the antimony-comprising phase change material.

22. The method of claim 21 comprising forming the antimony-comprising phase change material in direct physical touching contact with the inner electrode material, and forming the outer electrode material in direct physical touching contact with the antimony-comprising phase change material.

23. The method of claim 21 wherein forming the antimony-comprising phase change material produces the antimony-comprising phase change material to have no greater than 1 atomic percent of the oxygen.

24. The method of claim 21 wherein forming the antimony-comprising phase change material produces the antimony-comprising phase change material to have no detectable oxygen therein.

25. The method of claim 21 wherein the forming of the antimony-comprising phase change material comprises:

forming a monolayer onto the substrate from the $Sb(OR)_3$; and

after forming the monolayer, providing the reducing agent to the monolayer to remove ligands consisting or OR from the Sb to produce an Sb monolayer on the substrate.